

## Single N-Channel MOSFET

### DESCRIPTION

SMC3332 is the N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced trench technology devices are well suited for high efficiency fast switching applications, low in-line power loss are needed in small outline surface mount package.

### PART NUMBER INFORMATION

**SMC 3332 S - TR G**  
 a      b      c      d      e

- a : Company name.
- b : Product Serial number.
- c : Package code            S: SOT-23L
- d : Handling code          TR: Tape&Reel
- e : Green produce code    G: *RoHS Compliant*

### FEATURES

**$V_{DS} = 30V, I_D = 6A$**

$R_{DS(ON)} = 22m\Omega (Typ.) @ V_{GS} = 10V$   
 $R_{DS(ON)} = 26m\Omega (Typ.) @ V_{GS} = 4.5V$   
 $R_{DS(ON)} = 40m\Omega (Typ.) @ V_{GS} = 2.5V$

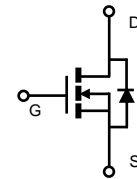
- ◆ Fast switch
- ◆ 2.5V Low gate drive applications
- ◆ 100% EAS Guaranteed

### APPLICATIONS

- ◆ Hand-Held Instruments
- ◆ Load Switch
- ◆ LED Applications



SOT-23L



### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ Unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Continuous Drain Current	$T_A = 25^\circ C$	6
		$T_A = 70^\circ C$	4.8
$I_{DM}$	Pulsed Drain Current <sup>A</sup>	24	A
$I_{AS}$	Avalanche Current <sup>C</sup>	12	A
EAS	Single Pulse Avalanche energy $L=0.1mH$ <sup>AE</sup>	7.2	mJ
$P_D$	Power Dissipation <sup>C</sup>	$T_A = 25^\circ C$	1.6
		$T_A = 70^\circ C$	1
$T_J$	Operation Junction Temperature	-55/150	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55/150	$^\circ C$

### THERMAL RESISTANCE

Symbol	Parameter	Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient <sup>B</sup>	$t \leq 10s$	80	$^\circ C/W$
	Thermal Resistance Junction to Ambient <sup>BD</sup>	Steady-State	120	

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ Unless otherwise noted)

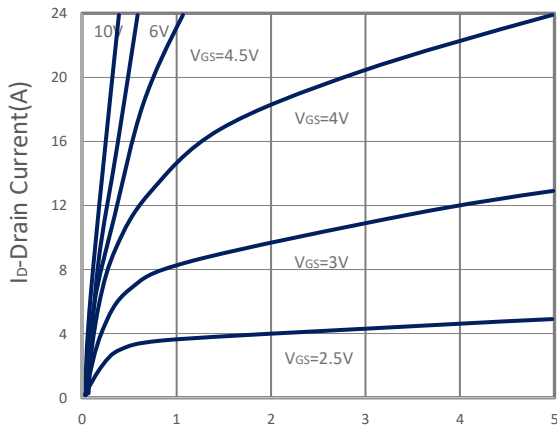
Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Parameters</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250 $\mu$ A	30			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 $\mu$ A	0.5	0.7	1	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = $\pm$ 12V			$\pm$ 100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25 $^\circ$ C			1	$\mu$ A
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =75 $^\circ$ C			10	
R <sub>DS(ON)</sub>	Drain-source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		22	26	m $\Omega$
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.8A		26	32	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.6A		40	48	
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A		7		S
<b>Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.75	1	V
I <sub>S</sub>	Continuous Source Current				3	A
<b>Dynamic and Switching Parameters</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>DS</sub> =15V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A		10.7	14.9	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			5.2	7	
Q <sub>gs</sub>	Gate-Source Charge			1.4	2	
Q <sub>gd</sub>	Gate-Drain Charge			1.8	2.5	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		432		pF
C <sub>oss</sub>	Output Capacitance			80		
C <sub>rss</sub>	Reverse Transfer Capacitance			60		
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =15, V <sub>GEN</sub> =10V, R <sub>G</sub> =6 $\Omega$ , I <sub>D</sub> =1A		3.8	7	nS
t <sub>r</sub>				12	23	
t <sub>d(off)</sub>	Turn-Off Time			24	46	
t <sub>f</sub>				8	15	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

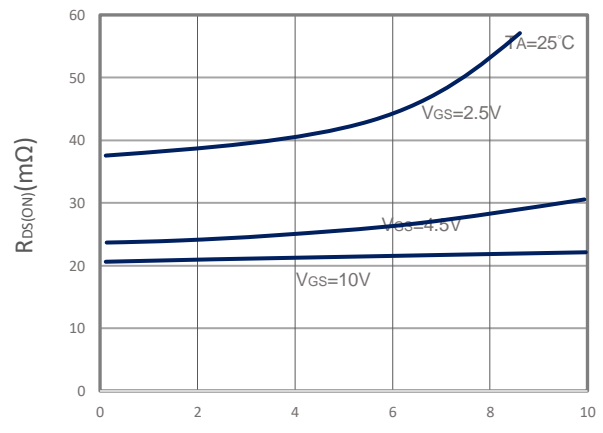
- Pulsed width limited by maximum junction temperature T<sub>J(MAX)</sub>=150 $^\circ$ C, initial temperature T<sub>J</sub>=25 $^\circ$ C.
- Measure the value in a still air environment at T<sub>A</sub>=25 $^\circ$ C using an installation mounted on a 1 in2 FR-4 board.
- Current Rating based t $\leq$ 10 sec thermal resistance rating.
- The R $\theta$ J<sub>A</sub> is the sum of the thermal resistance.
- The EAS data shows Maximum, tested and pulse width limited by maximum.

The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date. We assume no responsibility for any infringement of patents, patent rights, or other rights arising from the use of any information and circuitry in this datasheet.

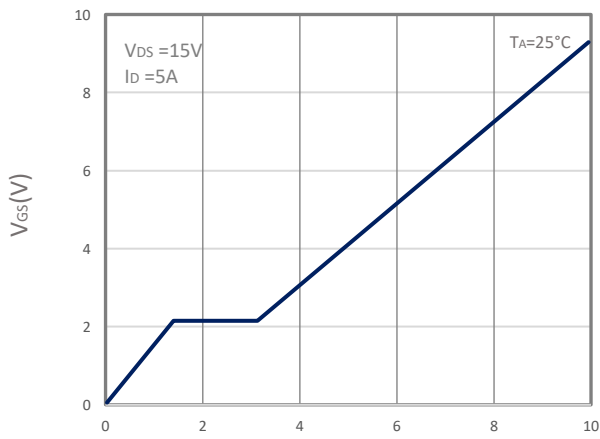
## TYPICAL CHARACTERISTICS



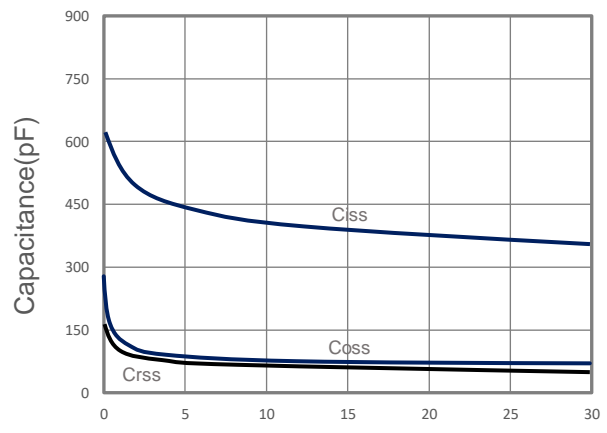
**Output Characteristics**



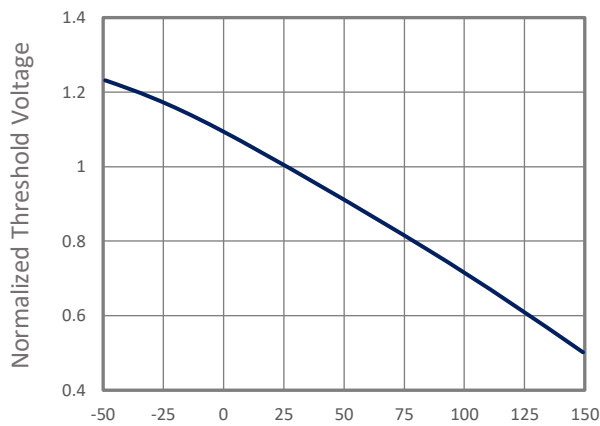
**Drain-Source On Resistance**



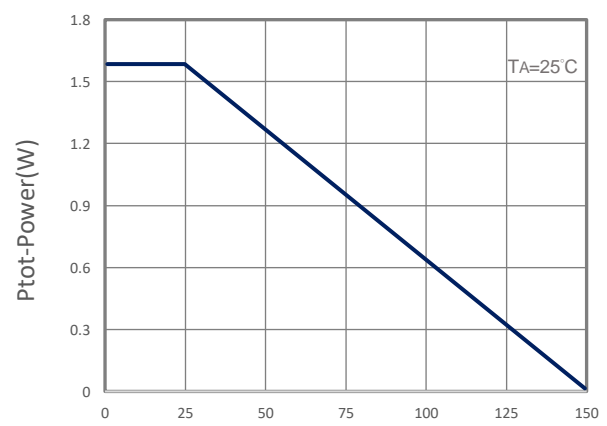
**Gate Charge**



**Capacitance**

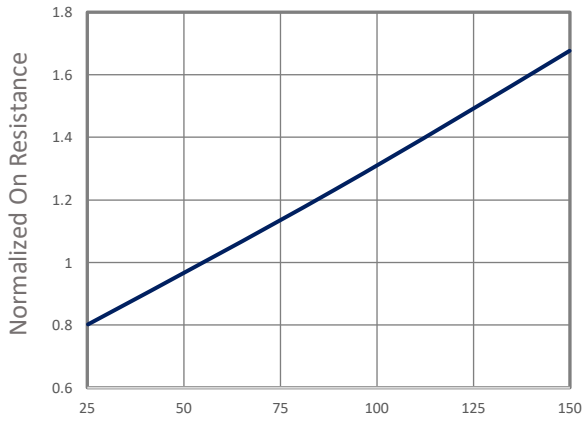


**Gate Threshold Voltage**

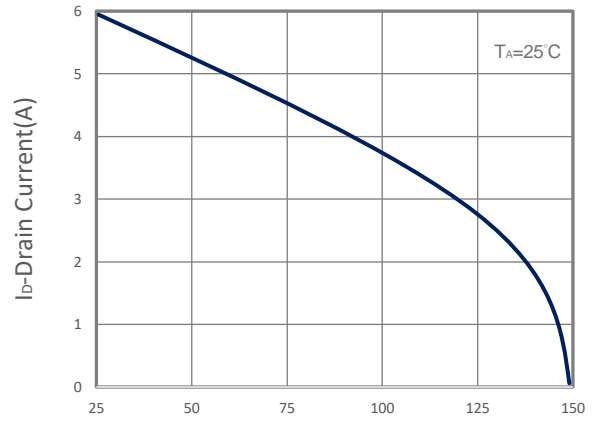


**Power Dissipation**

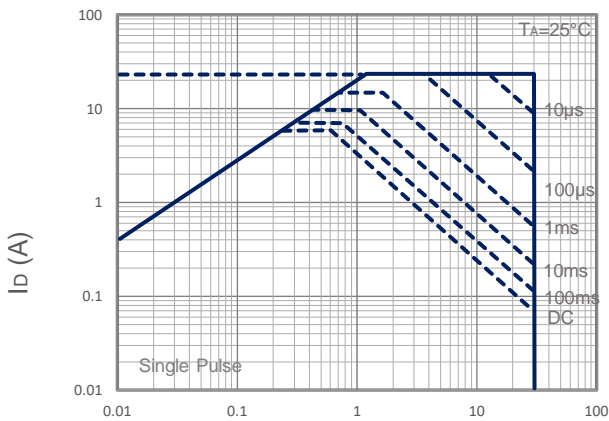
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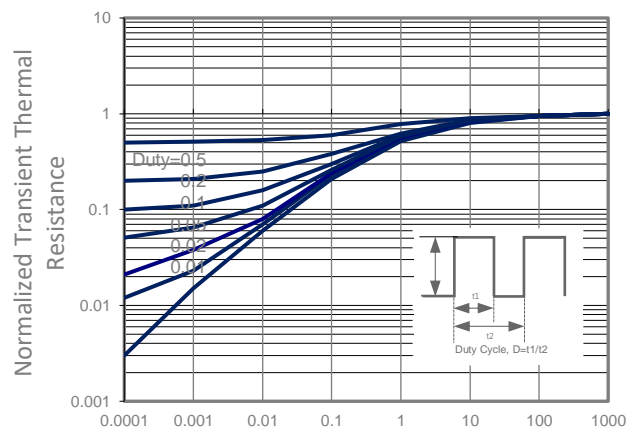
$R_{DS(ON)}$  vs Junction Temperature



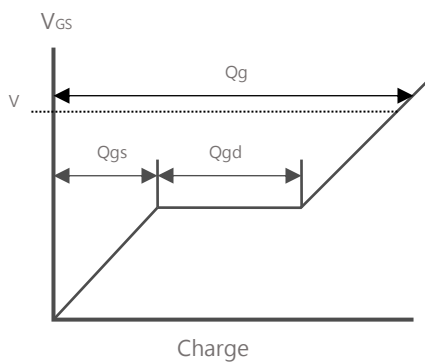
Drain Current vs  $T_j$



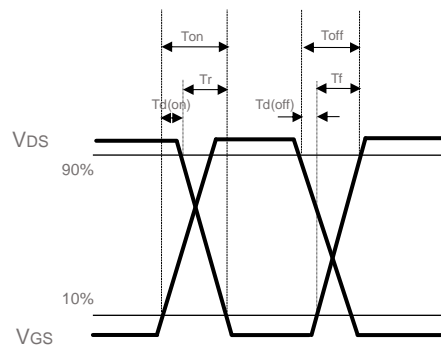
Maximum Safe Operation Area



Thermal Transient Impedance

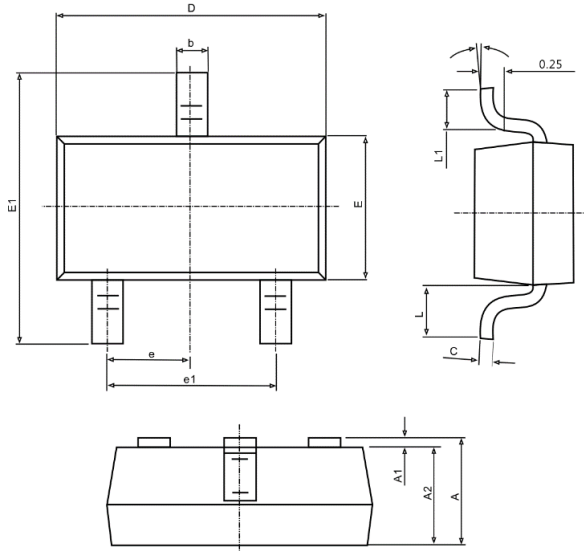


Gate Charge Waveform

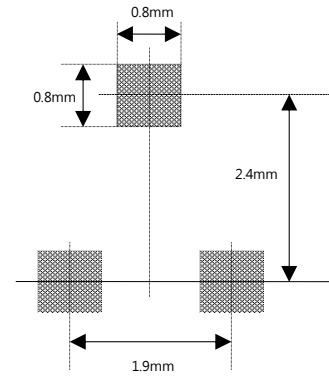


Switching Time Waveform

## ■ SOT-23L PACKAGE DIMENSIONS



Recommended Minimum Pad(mm)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.000	1.300	0.039	0.049
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.039	0.047
b	0.300	0.500	0.012	0.020
c	0.047	0.207	0.002	0.008
D	2.800	3.000	0.110	0.118
E	1.500	1.700	0.059	0.067
E1	2.600	3.000	0.102	0.118
e	0.950 TYP.		0.037 TYP.	
e1	1.900 TYP.		0.075 TYP.	
L1	0.250	0.550	0.010	0.022
θ	0°	8°	0°	8°